

EVVOSEMI[®]

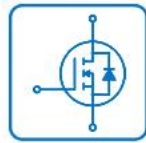
THINK CHANGE DO



ESD



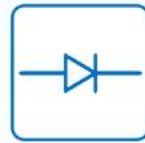
TVS



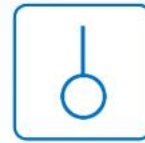
MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	MJ15022 / MJ15024
▶ Overseas	Part Number	MJ15022 / MJ15024
▶ Equivalent	Part Number	MJ15022 / MJ15024

EV is the abbreviation of name EVVO

Silicon NPN Power Transistors

DESCRIPTION

- Complement to Type PNP MJ15023/15025
- Excellent Safe Operating Area
- High DC current Gain

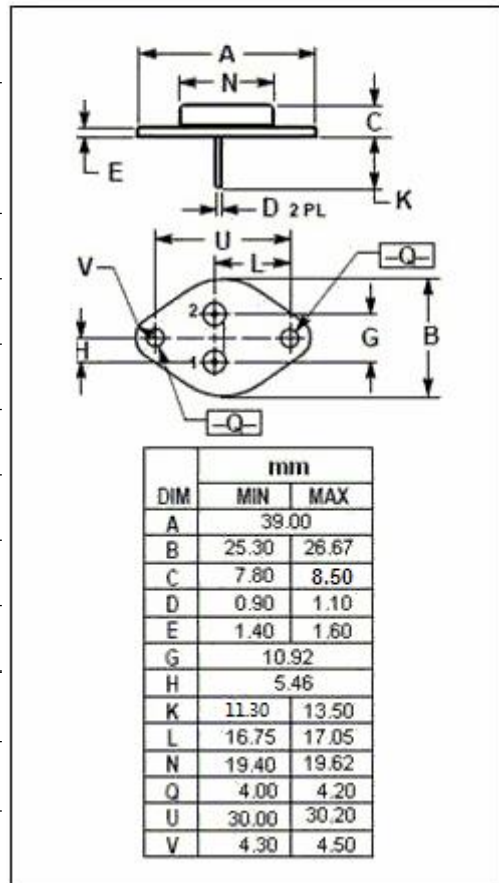
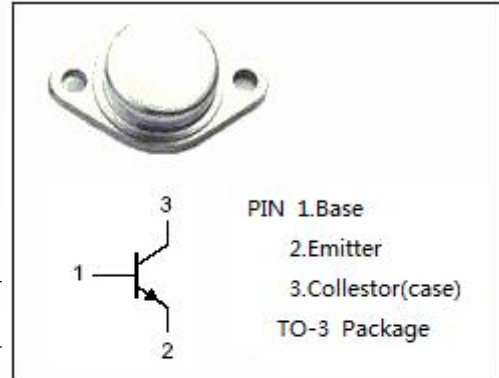
APPLICATIONS

- Designed for high power audio, disk head positioners and other linear applications

ABSOLUTE MAXIMUM RATINGS(T_C=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CB0}	Collector-Base Voltage	MJ15022	350	V
		MJ15024	400	
V _{CEO}	Collector-Emitter Voltage	MJ15022	200	V
		MJ15024	250	
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current-Continuous	16	A	
I _{CM} (1)	Collector Current-Peak	30	A	
I _B	Base Current-Continuous	5	A	
P _D	Total Power Dissipation @T _C =25°C	250	W	
T _J	Junction Temperature	-65~200	°C	
T _{stg}	Storage Temperature	-65~200	°C	
SYMBOL	PARAMETER	MAX	UNIT	
R _{th j-c}	Thermal Resistance, Junction to Case	0.70	°C/W	

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle _ 10%.



ELECTRICAL CHARACTERISTICS
T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CE0(SUS)} (1)	Collector-Emitter Sustaining Voltage	MJ15022	I _C = 50mA ; I _B = 0	200	V
		MJ15024		250	
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 0.8A		1.4	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 16A; I _B = 3.2A		4.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 8A ; V _{CE} = 4V		2.2	V
I _{CEO}	Collector Cutoff Current	MJ15022	V _{CE} = 150V; I _B = 0	0.5	mA
		MJ15024			
I _{CBO}	Collector Cutoff Current	MJ15022	V _{CB} = 200V; I _E = 0	0.25	mA
		MJ15024			
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0		0.5	mA
h _{FE-1}	DC Current Gain	I _C = 8A ; V _{CE} = 4V	15	60	
h _{FE-2}	DC Current Gain	I _C = 16A ; V _{CE} = 4V	5		
I _{s/b}	Second Breakdown Collector Current With Base Forward Biased	V _{CE} = 50Vdc, t=0.5 s, Nonrepetitive V _{CE} = 80Vdc, t=0.5 s, Nonrepetitive	5.0 2.0		A
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f _{test} = 1.0MHz	300		pF
f _T	Current-Gain—Bandwidth Product	I _C = 1A ; V _{CE} = 10V; f _{test} = 1.0MHz	4		MHz

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle _ 2%.

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